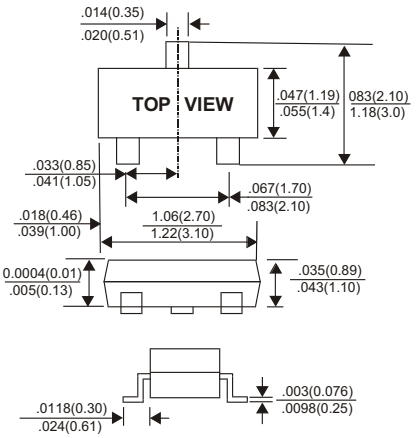
PAN202K / PANP202K / PAN217

SURFACE MOUNT SWITCHING DIODES

SWITCHING DIODE 100m AMPERRES 80 VOLTS

SOT-23



FEATURES

*Low Current Leakage

*Low Forward Voltage

*Ultra High Speed Switching

*Small Outline Surface Mount SOT-23 Package

MAXIMUM RATING (EACH DIODE)

Characteristic	Symbol	PAN202K	PANP202K	PAN217	Unit
Reverse Voltage	V_R	80			Volts
Forward Current	$I_{F(AV)}$	100			mA
Peak Forward Surge Current	I_{FSM}	300			mA

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board*1,TA=25°C Derate A ove 25°C	P_D	200 1.6	mW mW/°C
Thermal Resistance Junction to Am ient	$R_{\theta JA}$	625	°C / W
Junction and Storage Temperature	T_J, T_{stg}	-55 to + 150	°C

*1 ER-5=1.0x0.75x0.062 in

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ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Reverse Breakdown Voltage (I_R = 100 μA)	$V_{(BR)R}$	80	–	Volts
Reverse Voltage Leakage Current V_R=70V	I_R	–	0.1	μAdc
Diode Capacition(V_R=6vDC,f=1.0MHz)	C_D	–	3.5	pF
Forward Voltage I_F = 100mAdc	V_F	–	1.2	Vdc
Reverse Recovery Time(Figure1.) I_R = 5.0mAdc, V_R = 6.0Vdc	t_{rr}	–	4.0	nS

DEVICE MARKING

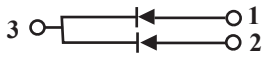
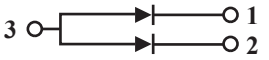
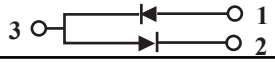
Item	Marking	Eqivalent Circuit diagram
P AN202K	A4	
P AP202K	A1	
P AN217	A7	

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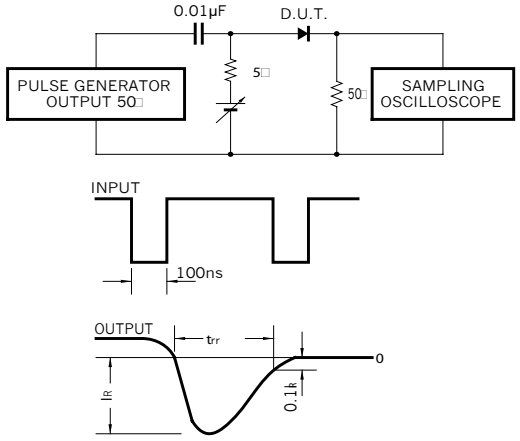
Figure 1. Recovery Time Equivalent Test Circuit



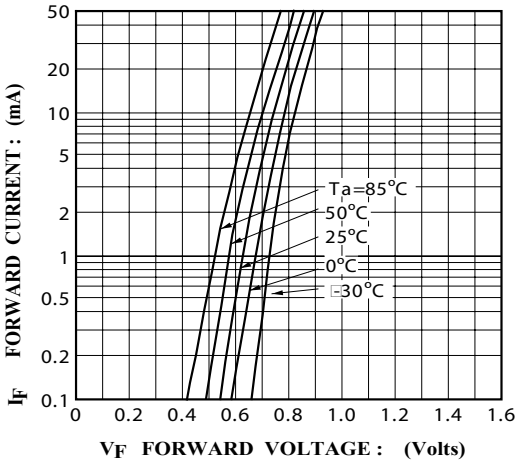


Fig.2 Forward characteristics

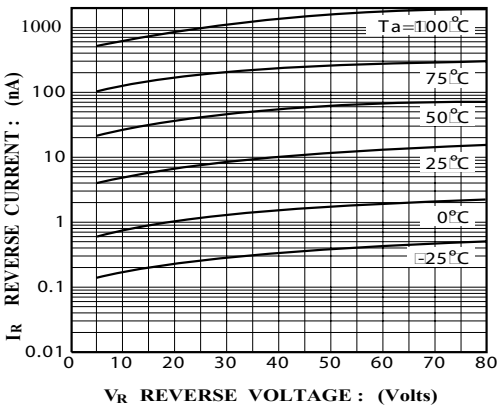


Fig.3 Reverse characteristics

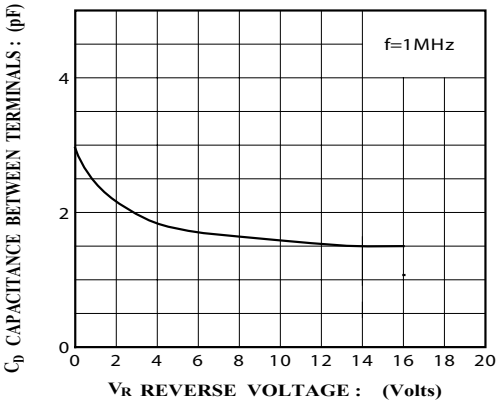


Fig.4 Capacitance